

1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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WeEn Semiconductors



Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT223 surface mountable plastic package. This "series D" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers.

2. Features and benefits

- 3Q technology for improved noise immunity
- Direct gate triggering from low power drivers and logic ICs
- High commutation capability with very sensitive gate
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Surface mountable package
- Triggering in three quadrants only
- · Very sensitive gate for easy logic level triggering

3. Applications

- Low power motor controls
- Small inductive loads e.g. solenoids, door locks, water valves
- Small loads in large white goods

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	-	9	Α
T _j	junction temperature		-	-	125	°C
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 111 ^{\circ}\text{C}$; Fig. 2; Fig. 3	-	-	8.0	Α
Static characte	eristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 9$	0.25	-	5	mA





Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 9</u>	0.25	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 9}}$	0.25	-	5	mA
Dynamic char	acteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	200	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 0.8 A; dV_{com}/dt = 10 V/ μ s; gate open circuit	0.5	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	4	T2
2	T2	main terminal 2		sym051
3	G	gate		J
4	mb	mounting base; connected to main terminal 2	☐1 ☐2 ☐3 SC-73 (SOT223)	

6. Ordering information

Table 3. Ordering information

Type number Package				
	Name	Description	Version	
BTA2008W-800D	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223	

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 111 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	0.8	А
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	9	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	9.9	А
l ² t	I ² t for fusing	t_p = 10 ms; SIN	-	0.41	A ² s
dI _T /dt	rate of rise of on-state current	$I_T = 1.5 \text{ A}$; $I_G = 20 \text{ mA}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I _{GM}	peak gate current		-	2	Α
P _{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

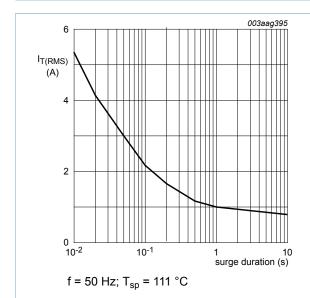


Fig. 1. RMS on-state current as a function of surge duration; maximum values

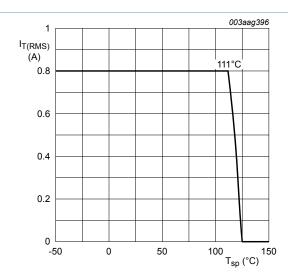


Fig. 2. RMS on-state current as a function of lead temperature; maximum values

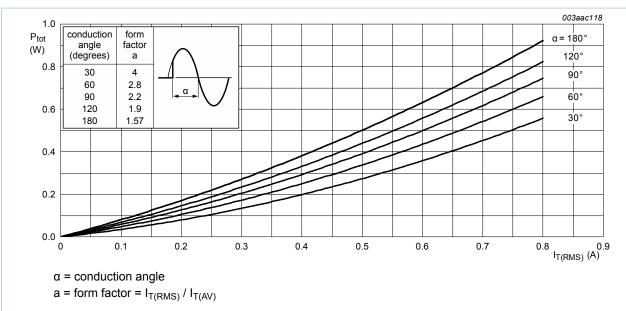


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

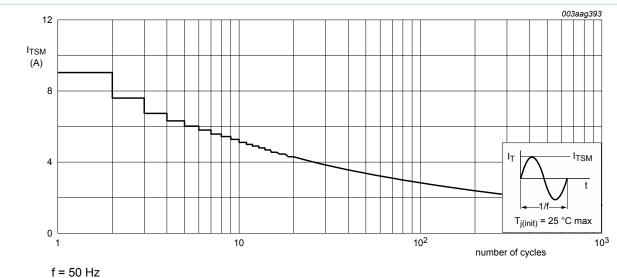
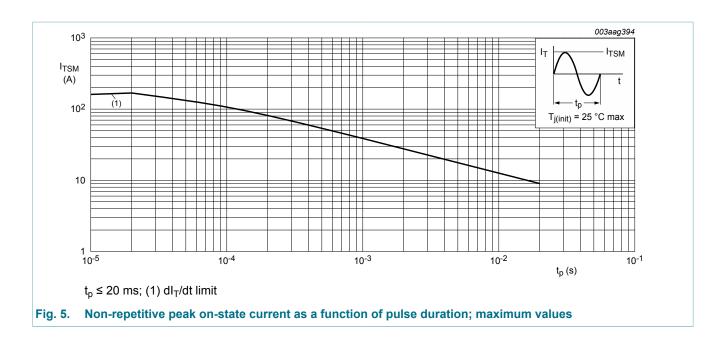


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	full cycle; Fig. 6	-	-	15	K/W
R _{th(j-a)}	thermal resistance from junction to	in free air; printed-circuit board mounted: minimum footprint; Fig. 7	-	156	-	K/W
	ambient	in free air; printed-circuit board mounted: minimum pad area; Fig. 8	-	70	-	K/W

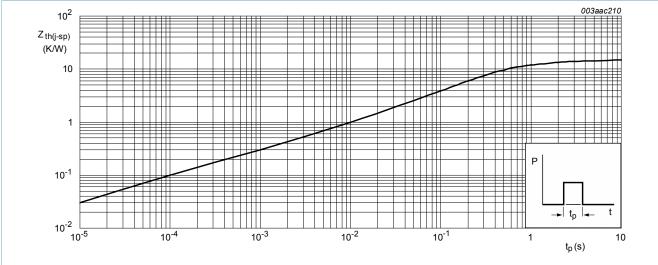
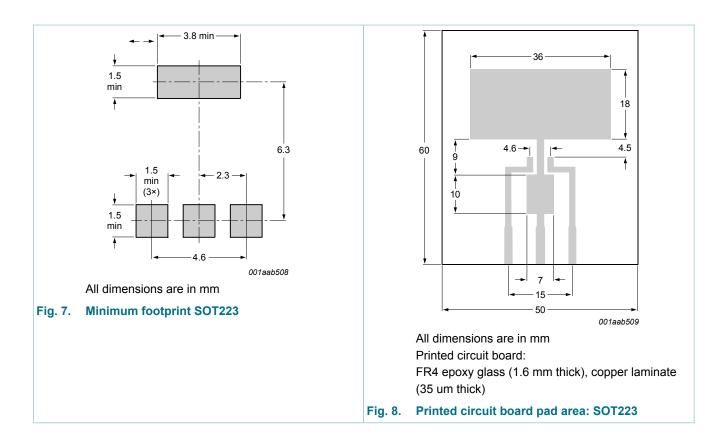


Fig. 6. Transient thermal impedance from junction to solder point as a function of pulse width

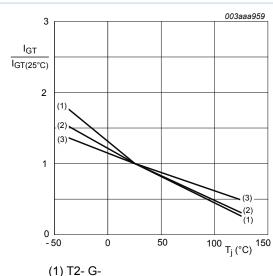


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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		'			
I _{GT} g	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 9$	0.25	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 9$	0.25	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 9}}$	0.25	-	5	mA
I _L latching current	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 10$	-	-	10	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 10$	-	-	20	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 10$	-	-	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 11</u>	-	-	10	mA
V _T	on-state voltage	I _T = 0.85 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.35	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 13	-	0.9	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 13	0.2	0.3	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic cl	haracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; gate open circuit	200	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 0.8 A; dV_{com}/dt = 10 V/ μ s; gate open circuit	0.5	-	-	A/ms



- (2) T2+ G-
- (3) T2+ G+

Fig. 9. Normalized gate trigger current as a function of junction temperature

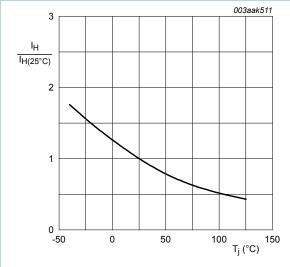


Fig. 11. Normalized holding current as a function of junction temperature

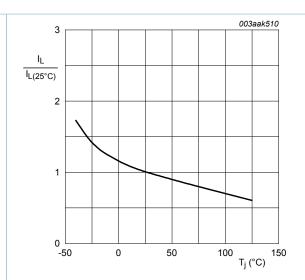
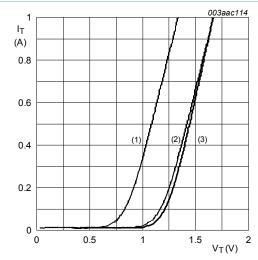


Fig. 10. Normalized latching current as a function of junction temperature



- V_o = 0.835 V; R_s = 0.50 Ω
- (1) T_j = 125 °C; typical values
- (2) T_i = 125 °C; maximum values
- (3) T_i = 25 °C; maximum values

Fig. 12. On-state current as a function of on-state voltage

Product data sheet

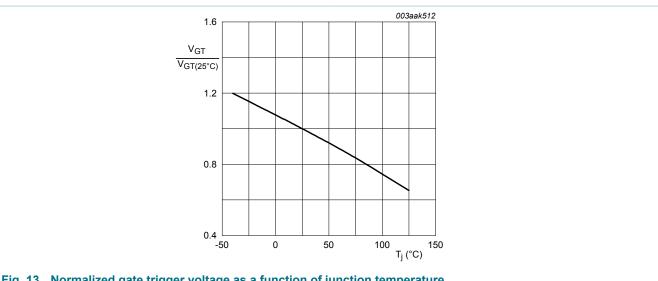
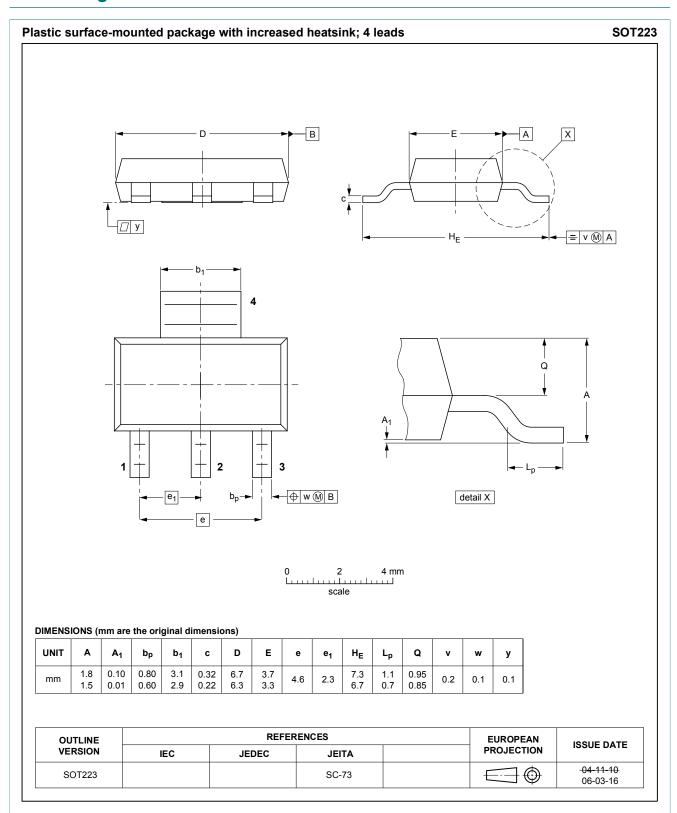


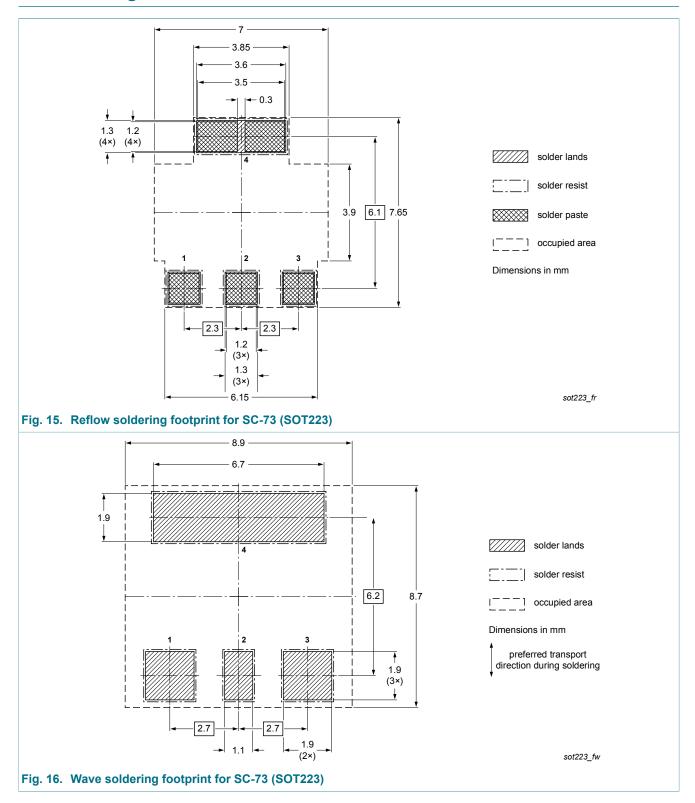
Fig. 13. Normalized gate trigger voltage as a function of junction temperature

10. Package outline



Product data sheet

11. Soldering



12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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